

FDMC007N30D

MOSFET, Dual N-Channel, POWERTRENCH®

Q1: 30 V, 11.6 mΩ; Q2: 30 V, 6.4 mΩ

General Description

This device includes two specialized N-Channel MOSFETs in a dual Power33 (3mm × 3mm MLP) package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous MOSFET (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 11.6 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$
- Max $r_{DS(on)}$ = 13.3 mΩ at $V_{GS} = 4.5\text{ V}$, $I_D = 9\text{ A}$

Q2: N-Channel

- Max $r_{DS(on)}$ = 6.4 mΩ at $V_{GS} = 10\text{ V}$, $I_D = 16\text{ A}$
- Max $r_{DS(on)}$ = 7.0 mΩ at $V_{GS} = 4.5\text{ V}$, $I_D = 15\text{ A}$
- RoHS Compliant

Applications

- Mobile Computing
- Mobile Internet Devices
- General Purpose Point of Load

MOSFET MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

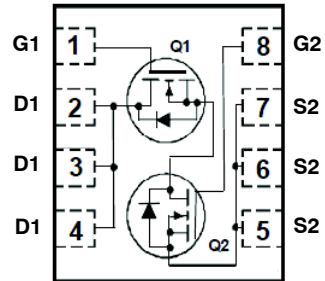
Symbol	Parameter	Q1	Q2	Unit
V_{DS}	Drain to Source Voltage	30	30	V
V_{GS}	Gate to Source Voltage (Note 4)	±12	±12	V
I_D	Drain Current:			A
	- Continuous, $T_C = 25^\circ\text{C}$ (Note 6)	29	46	
	- Continuous, $T_C = 100^\circ\text{C}$ (Note 6)	18	29	
	- Continuous, $T_A = 25^\circ\text{C}$ (Note 1a)	10	16	
	- Pulsed (Note 5)	113 (Note 1a)	302 (Note 1b)	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	24	54	mJ
P_D	Power Dissipation for Single Operation:			W
	$T_A = 25^\circ\text{C}$	1.9 (Note 1a)	2.5 (Note 1b)	
	$T_A = 25^\circ\text{C}$	0.7 (Note 1c)	1.0 (Note 1d)	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150		$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

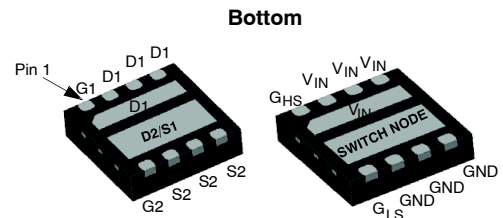


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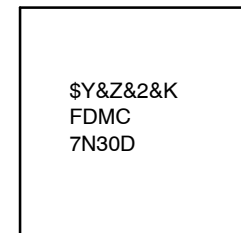


Dual N-Channel MOSFET



WDFN8 3x3
CASE 511DE

MARKING DIAGRAM



\$Y = ON Semiconductor Logo
 &Z = Assembly Plant Code
 &2 = Data Code (Year & Week)
 &K = Lot
 FDMC7N30D = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FDMC007N30D

PACKAGE MARKING AND ORDERING INFORMATION

Device Marking	Device	Package	Quantity
FDMC7N30D	FDMC007N30D	WDFN-8 (Power 33)	3000/Tape&Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case	8.2	6.1	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	65 (Note 1a)	50 (Note 1b)	
		180 (Note 1c)	125 (Note 1d)	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$ $I_D = 250 \mu\text{A}$, $V_{GS} = 0 \text{ V}$	Q1 Q2	30 30			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C $I_D = 250 \mu\text{A}$, referenced to 25°C	Q1 Q2		15 16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}$, $V_{GS} = 0 \text{ V}$	Q1 Q2			1 1	μA
I_{GSS}	Gate to Source Leakage Current, Forward	$V_{GS} = \pm 12 \text{ V}$, $V_{DS} = 0 \text{ V}$	Q1 Q2			± 100 ± 100	nA

ON CHARACTERISTICS

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$ $V_{GS} = V_{DS}$, $I_D = 250 \mu\text{A}$	Q1 Q2	1.0 1.0	1.3 1.8	3.0 3.0	V
$\Delta V_{GS(th)} / \Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, referenced to 25°C $I_D = 250 \mu\text{A}$, referenced to 25°C	Q1 Q2		-4 -4		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 10 \text{ A}$ $V_{GS} = 4.5 \text{ V}$, $I_D = 9 \text{ A}$ $V_{GS} = 10 \text{ V}$, $I_D = 10 \text{ A}$, $T_J = 125^\circ\text{C}$	Q1		7.7 8.9 10.8	11.6 13.3 16.3	m Ω
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}$, $I_D = 16 \text{ A}$ $V_{GS} = 4.5 \text{ V}$, $I_D = 15 \text{ A}$ $V_{GS} = 10 \text{ V}$, $I_D = 16 \text{ A}$, $T_J = 125^\circ\text{C}$	Q2		4.4 5.4 6.2	6.4 7.0 9.0	m Ω
g_{FS}	Forward Transconductance	$V_{DD} = 5 \text{ V}$, $I_D = 10 \text{ A}$ $V_{DD} = 5 \text{ V}$, $I_D = 16 \text{ A}$	Q1 Q2		46 70		S

DYNAMIC CHARACTERISTICS

C_{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	Q1 Q2		792 1685	1110 2360	pF
C_{oss}	Output Capacitance		Q1 Q2		230 467	325 655	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		20 36	30 50	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	2.0 1.2	4.0 2.4	Ω

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted) (continued)

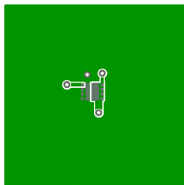
Symbol	Parameter	Test Condition	Type	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS							
t _{d(on)}	Turn-On Delay Time	Q1 V _{DD} = 15 V, I _D = 10 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	Q1		7	14	ns
t _r	Rise Time		Q2		2	10	ns
t _{d(off)}	Turn-Off Delay Time	Q2 V _{DD} = 15 V, I _D = 16 A, V _{GS} = 10 V, R _{GEN} = 6 Ω	Q1		19	33	ns
t _f	Fall Time		Q2		2	10	ns
Q _{g(TOT)}	Total Gate Charge	V _{GS} = 0 V to 10 V Q1 V _{DD} = 15 V, V _{GS} = 0 V to 4.5 V I _D = 10 A Q2 V _{DD} = 15 V, I _D = 16 A	Q1		12	17	nC
Q _{gs}	Gate to Source Charge		Q2		24	34	nC
Q _{gd}	Gate to Drain "Miller" Charge		Q1		5.5	7.7	nC
			Q2		11	16	nC
		Q1		1.7		nC	
		Q2		4.4		nC	
		Q1		1.3		nC	
		Q2		2.7		nC	

DRAIN-SOURCE DIODE CHARACTERISTICS

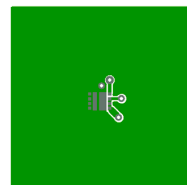
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = 10 A (Note 2) V _{GS} = 0 V, I _S = 1.5 A (Note 2) V _{GS} = 0 V, I _S = 16 A (Note 2) V _{GS} = 0 V, I _S = 2 A (Note 2)	Q1 Q1 Q2 Q2		0.85 0.75 0.83 0.73	1.2 1.2 1.2 1.2	V
t _{rr}	Reverse Recovery Time	Q1 I _F = 10 A, di/dt = 100 A/μs	Q1 Q2		17 27	31 42	ns
Q _{rr}	Reverse Recovery Charge	Q2 I _F = 16 A, di/dt = 100 A/μs	Q1 Q2		5 10	10 20	nC

NOTES:

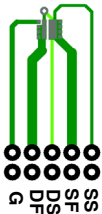
- R_{θJA} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 × 1.5 in. board of FR-4 material. R_{θCA} is determined by the user's board design.



a. 65 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 50 °C/W when mounted on a 1 in² pad of 2 oz copper.



c. 180 °C/W when mounted on a minimum pad of 2 oz copper.



d. 125 °C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
- Q1: E_{AS} of 24 mJ is based on starting T_J = 25°C, L = 3 mH, I_{AS} = 4 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 13 A. Q2: E_{AS} of 54 mJ is based on starting T_J = 25°C, L = 3 mH, I_{AS} = 6 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} = 22 A.
- As an N-ch device, the negative V_{gs} rating is for low duty cycle pulse occurrence only. No continuous rating is implied.
- Pulsed I_d please refer to Figure 11 and Figure. 24 SOA graph for more details.
- Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

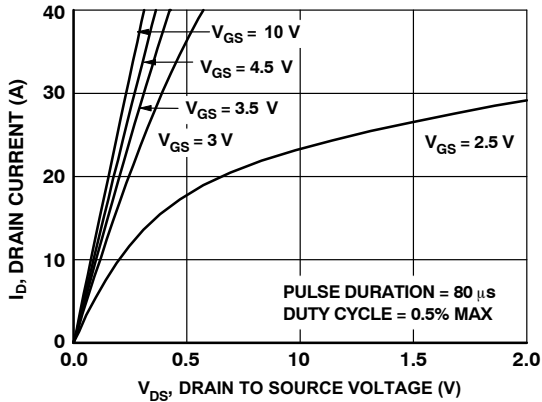


Figure 1. On Region Characteristics

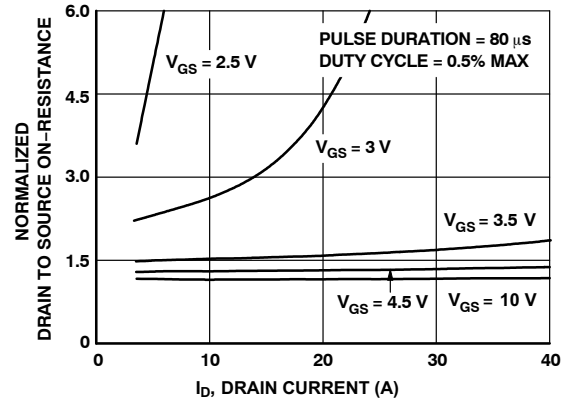


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

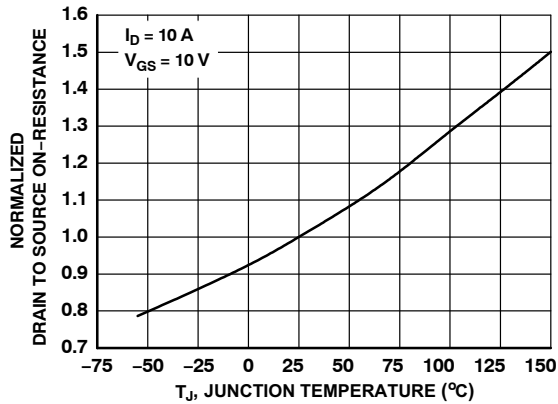


Figure 3. Normalized On Resistance vs. Junction Temperature

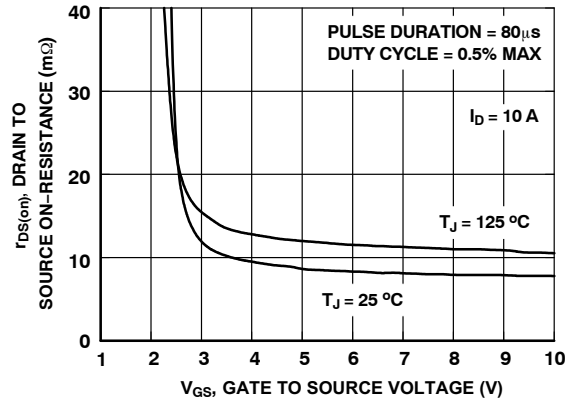


Figure 4. On-Resistance vs. Gate to Source Voltage

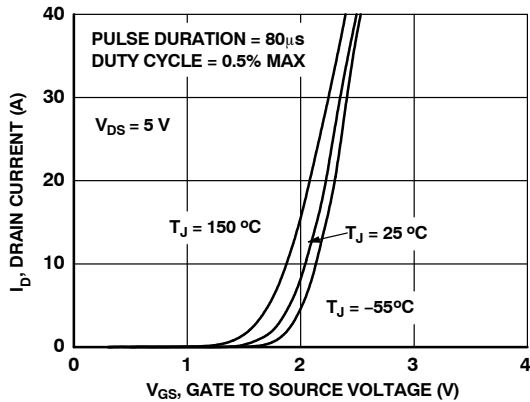


Figure 5. Transfer Characteristics

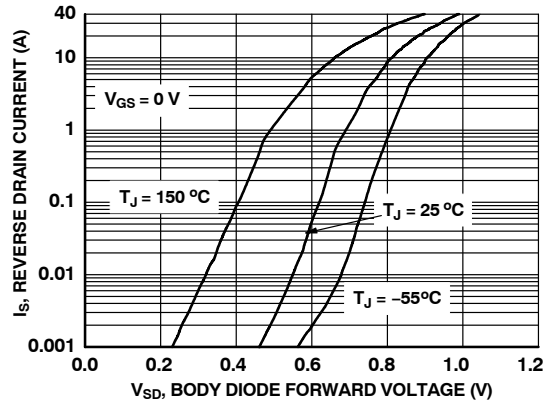


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

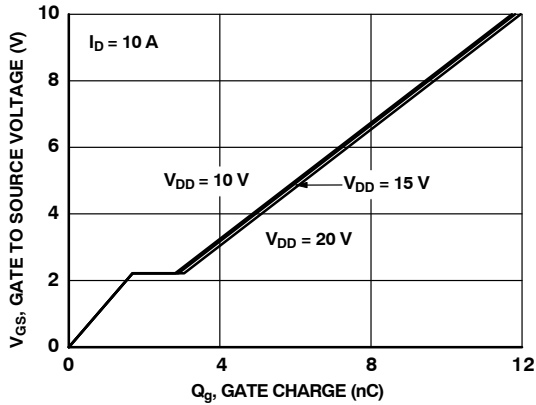


Figure 7. Gate Charge Characteristics

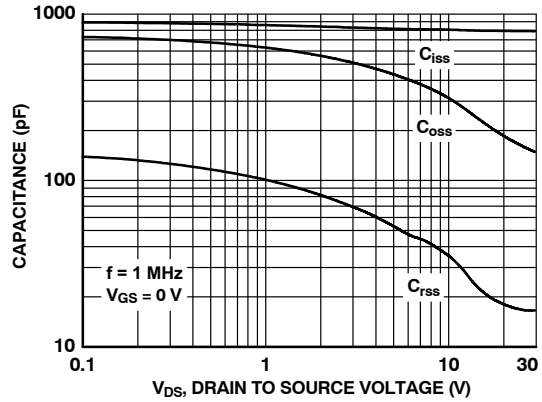


Figure 8. Capacitance vs. Drain to Source Voltage

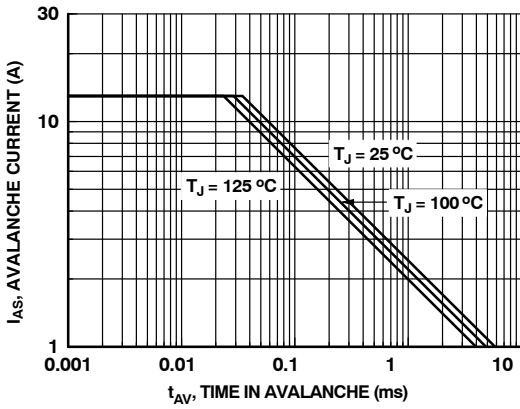


Figure 9. Unclamped Inductive Switching Capability

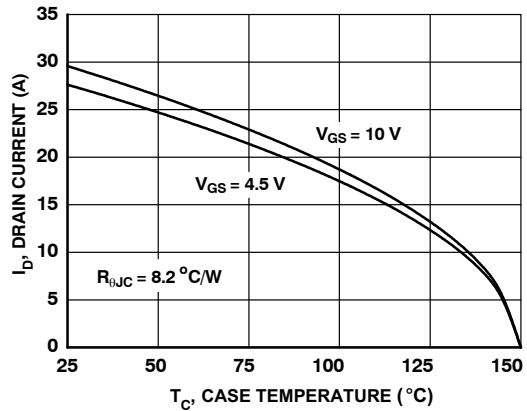


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

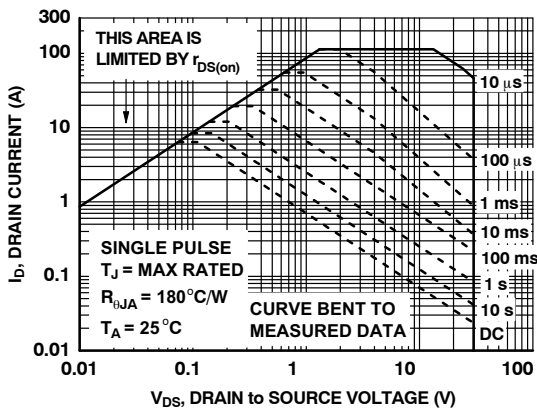


Figure 11. Forward Bias Safe Operating Area

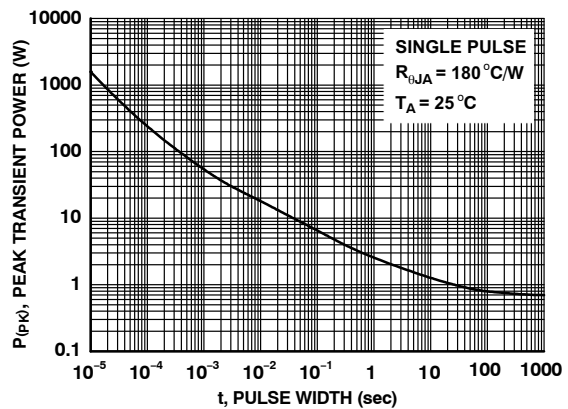


Figure 12. Single Pulse Maximum Power Dissipation

FDMC007N30D

TYPICAL CHARACTERISTICS (Q1 N-CHANNEL) (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

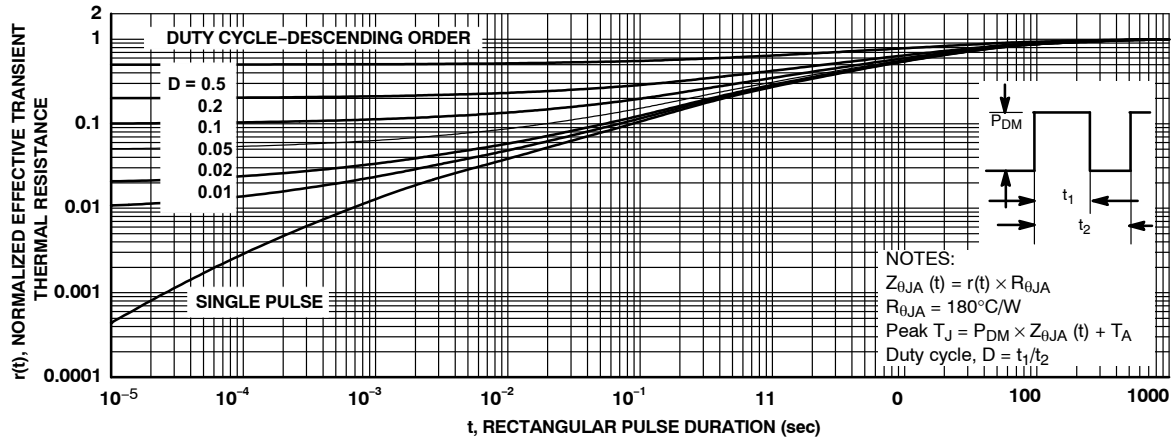


Figure 13. Junction-to-Ambient Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

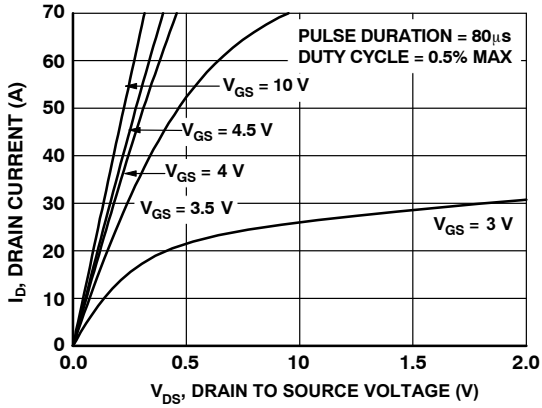


Figure 14. On Region Characteristics

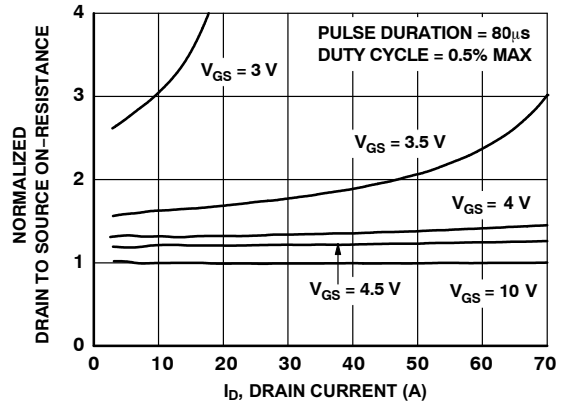


Figure 15. Normalized On-Resistance vs. Drain Current and Gate Voltage

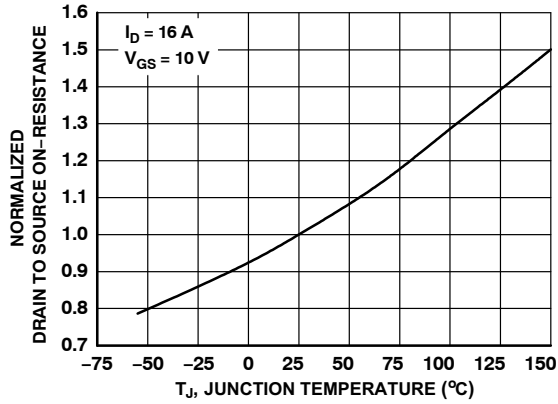


Figure 16. Normalized On Resistance vs. Junction Temperature

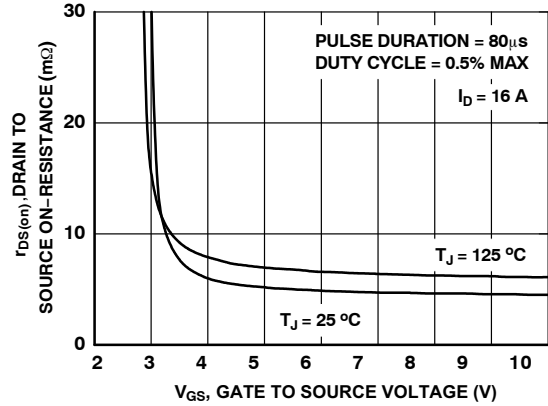


Figure 17. On-Resistance vs. Gate to Source Voltage

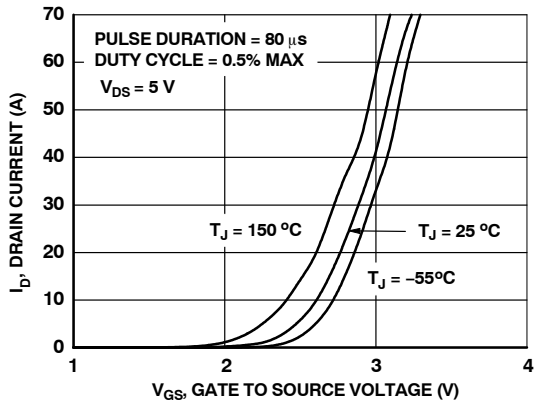


Figure 18. Transfer Characteristics

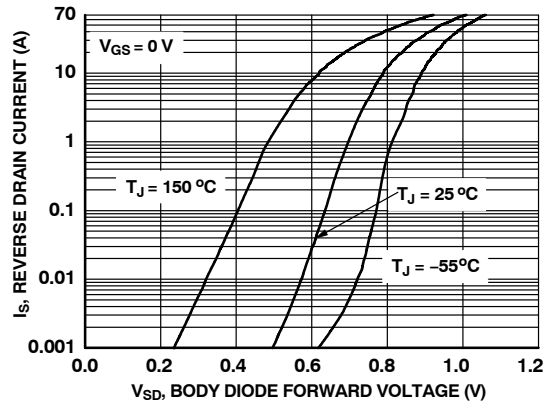


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

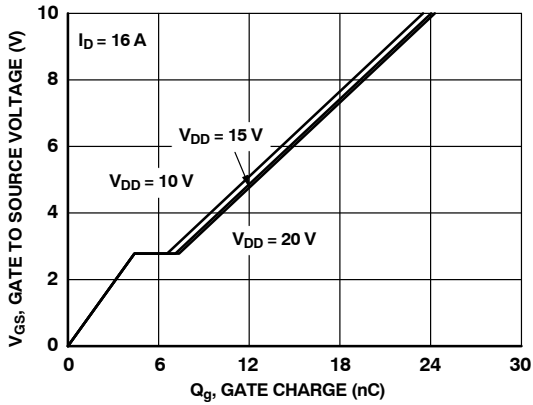


Figure 20. Gate Charge Characteristics

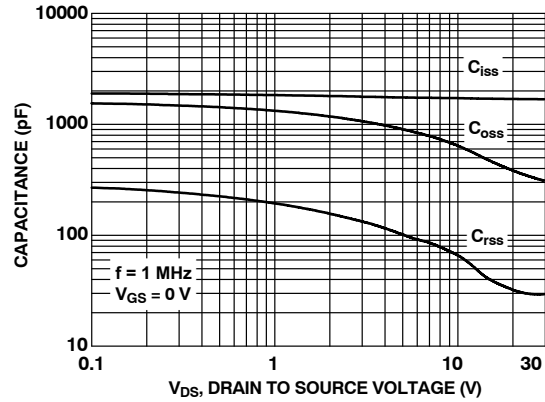


Figure 21. Capacitance vs. Drain to Source Voltage

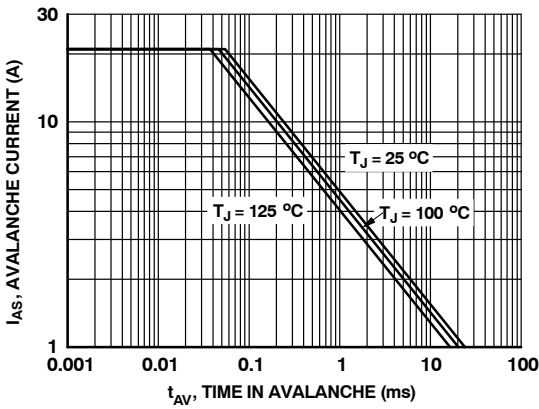


Figure 22. Unclamped Inductive Switching Capability

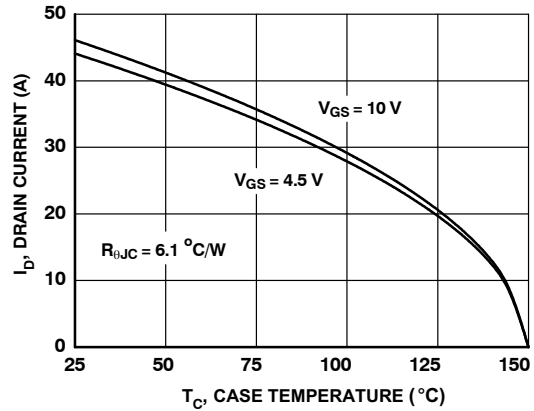


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

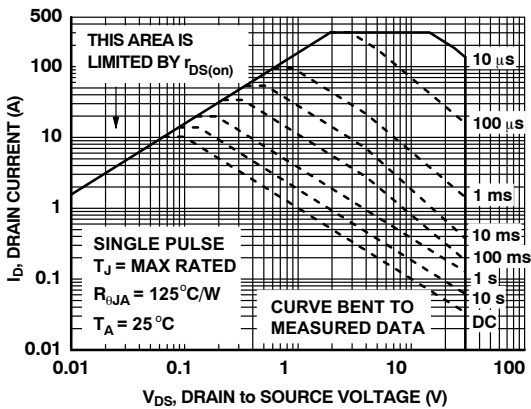


Figure 24. Forward Bias Safe Operating Area

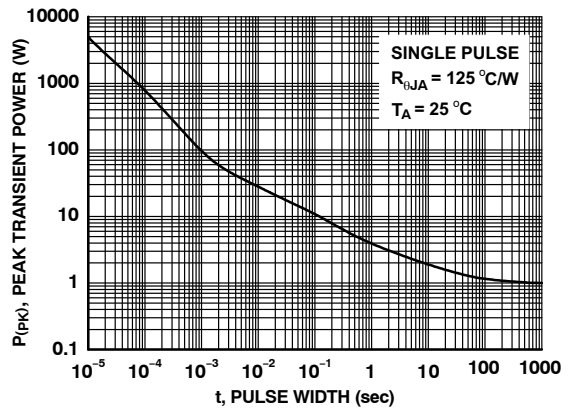


Figure 25. Single Pulse Maximum Power Dissipation

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TYPICAL CHARACTERISTICS (Q2 N-CHANNEL) (continued)

($T_J = 25^\circ\text{C}$ unless otherwise noted)

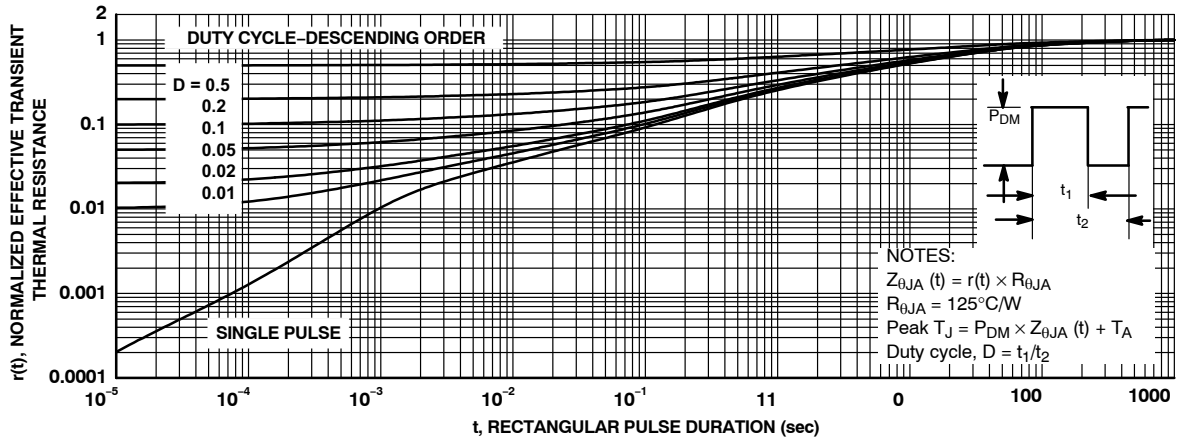


Figure 26. Junction-to-Ambient Transient Thermal Response Curve

MECHANICAL CASE OUTLINE

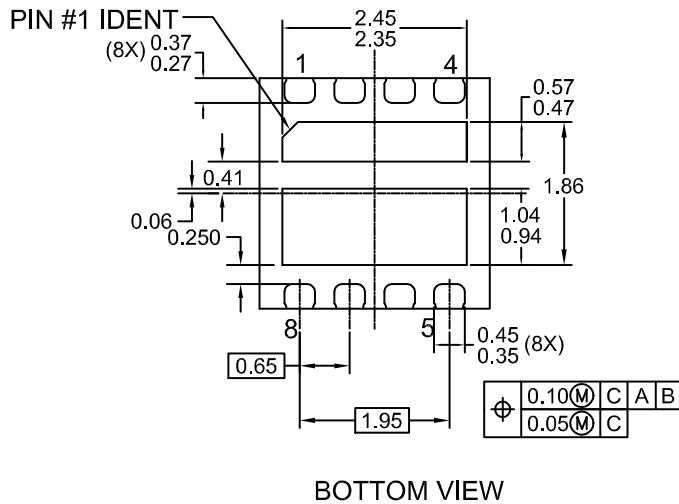
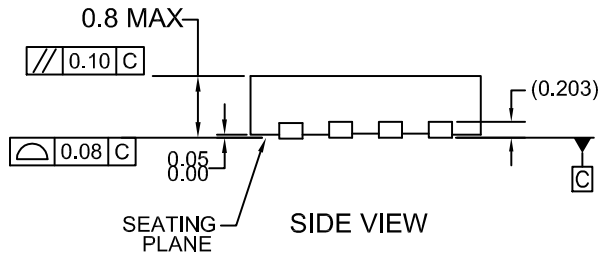
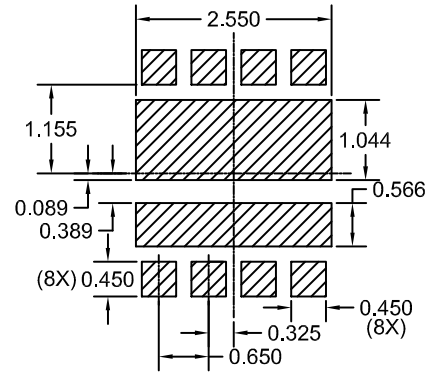
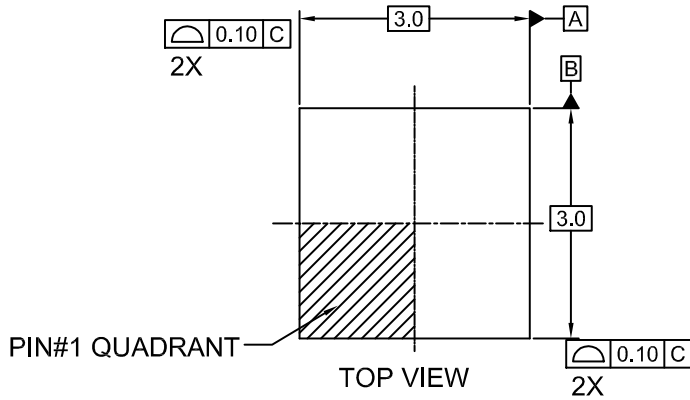
PACKAGE DIMENSIONS

ON Semiconductor®



WDFN8 3x3, 0.65P
CASE 511DE
ISSUE O

DATE 31 AUG 2016



NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994

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